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SEMICONDUCTOR



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AON6362-MS

Product specification

Description

The AON6362-MS uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

Features

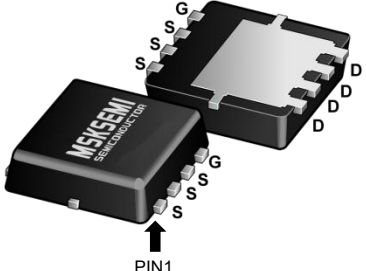
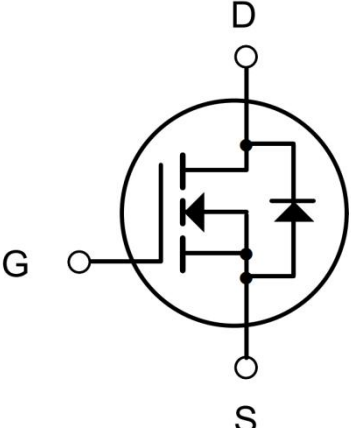

$V_{DS} = 30V$ $I_D = 70A$

$R_{DS(ON)} < 7m\Omega$ $V_{GS} = 10V$

Application

- Battery protection
- Load switch
- Uninterruptible power supply

Reference News

PACKAGE OUTLINE	N-Channel MOSFET	Marking
 <p>DFN5X6-8L</p>		

Absolute Maximum Ratings (TC=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain- Source Voltage	30	V
V_{GS}	Gate- Source Voltage	± 20	V
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$ ¹	70	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$ ¹	40	A
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$ ¹	30	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$ ¹	18	A
I_{DM}	Pulsed Drain Current ²	140	A
EAS	Single Pulse Avalanche Energy ³	115.2	mJ
I_{AS}	Avalanche Current	48	A
$P_D @ T_C = 25^\circ C$	Total Power Dissipation ⁴	59	W
$P_D @ T_A = 25^\circ C$	Total Power Dissipation ⁴	2	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C
$R_{\theta JA}$	Thermal Resistance Junction- Ambient ¹	62	°C/ W
$R_{\theta JC}$	Thermal Resistance Junction- Case ¹	2.1	°C/ W

Electrical Characteristics (TC=25°C Unless Otherwise Noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain- Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	30	---	---	V
ΔBV _{DSS} /ΔT _J	BVDSS Temperature Coefficient	Reference to 25°C , I _D =1mA	---	0.028	---	V/°C
R _{DS(ON)}	Static Drain-Source On- Resistance ²	V _{GS} =10V , I _D =30A	---	5.7	7	mΩ
		V _{GS} =4.5V , I _D =15A	---	11	13	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.2	---	2.5	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	-6.16	---	mV/°C
I _{DSS}	Drain- Source Leakage Current	V _{DS} =24V , V _{GS} =0V , T _J =25°C	---	---	1	uA
		V _{DS} =24V , V _{GS} =0V , T _J =55°C	---	---	5	
I _{GSS}	Gate- Source Leakage Current	V _{GS} = ±20V , V _{DS} =0V	---	---	± 100	nA
g _{fs}	Forward Transconductance	V _{DS} =5V , I _D =30A	---	43	---	S
R _g	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz	---	1.7	---	Ω
Q _g	Total Gate Charge (4.5V)	V _{DS} =15V , V _{GS} =4.5V , I _D =15A	---	20	---	nC
Q _{gs}	Gate- Source Charge		---	7.6	---	
Q _{gd}	Gate- Drain Charge		---	7.2	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =15V , V _{GS} =10V , R _G =3.3 I _D =15A	---	7.8	---	ns
T _r	Rise Time		---	15	---	
T _{d(off)}	Turn-Off Delay Time		---	37.3	---	
T _f	Fall Time		---	10.6	---	
C _{iss}	Input Capacitance	V _{DS} =15V , V _{GS} =0V , f=1MHz	---	2295	---	pF
C _{oss}	Output Capacitance		---	267	---	
C _{rss}	Reverse Transfer Capacitance		---	210	---	
I _S	Continuous Source Current ^{1,5}	V _G =V _D =0V , Force Current	---	---	81	A
I _{SM}	Pulsed Source Current ^{2,5}		---	---	160	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _S =1A , T _J =25°C	---	---	1	V
t _{rr}	Reverse Recovery Time	I _F =30A , dI/dt=100A/μs , T _J =25°C	---	14	---	nS
Q _{rr}	Reverse Recovery Charge		---	5	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The EAS data shows Max. rating . The test condition is V_{DD}=25V,V_{GS}=10V,L=0. 1mH,I_{AS}=48A
- 4.The power dissipation is limited by 150C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

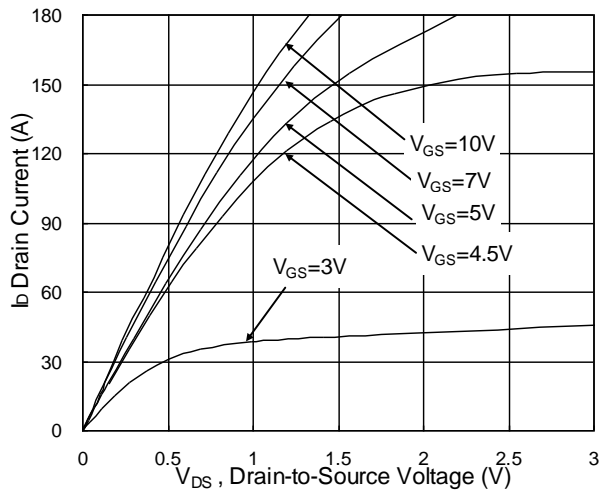


Fig.1 Typical Output Characteristics

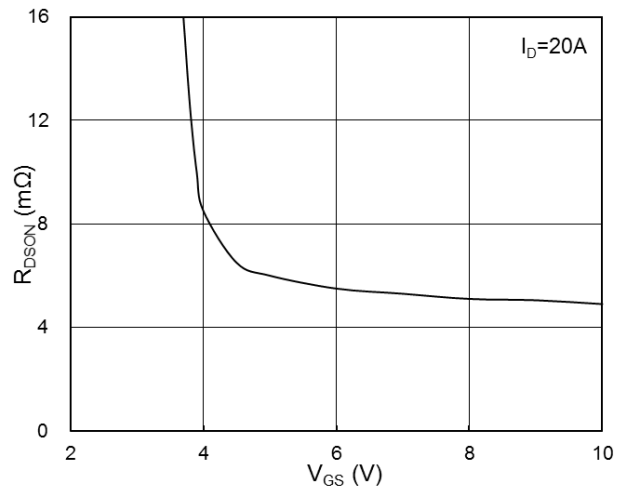


Fig.2 On-Resistance vs. G-S Voltage

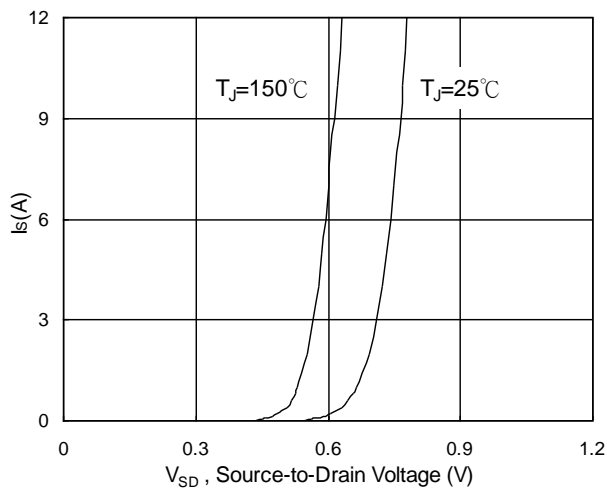


Fig.3 Forward Characteristics of Reverse

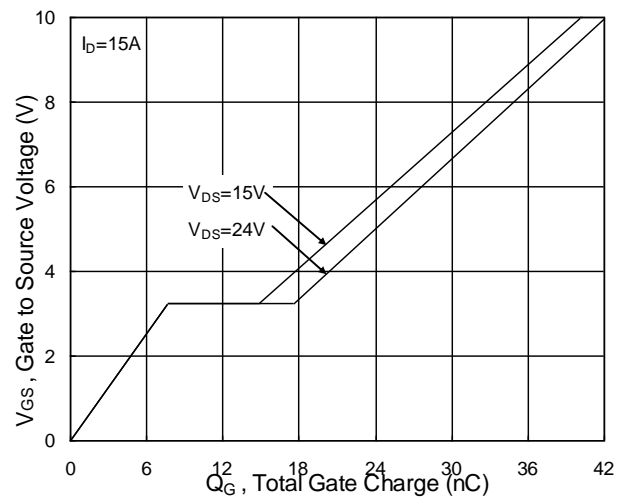


Fig.4 Gate-Charge Characteristics

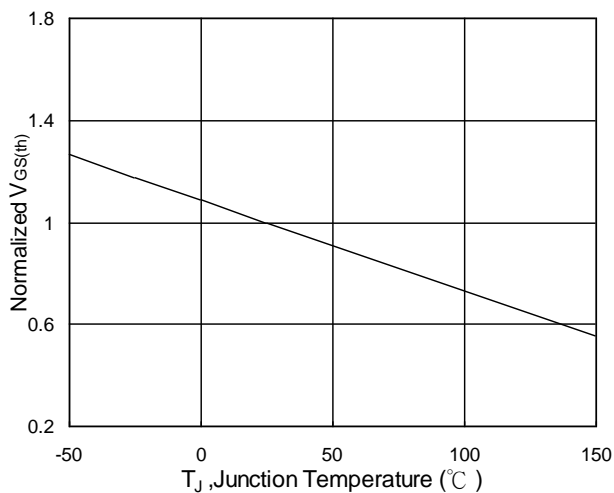


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

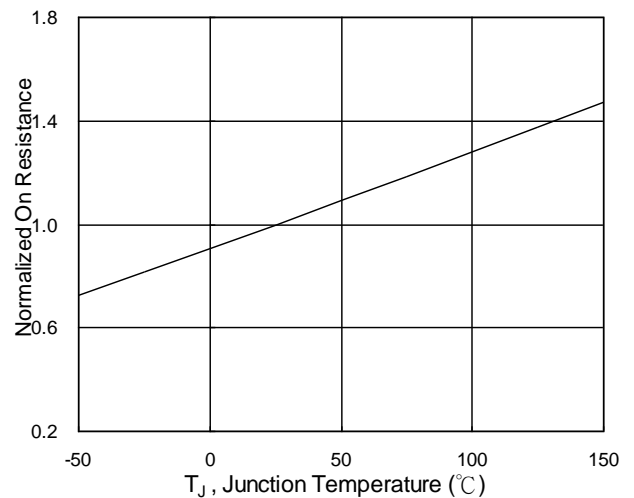


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

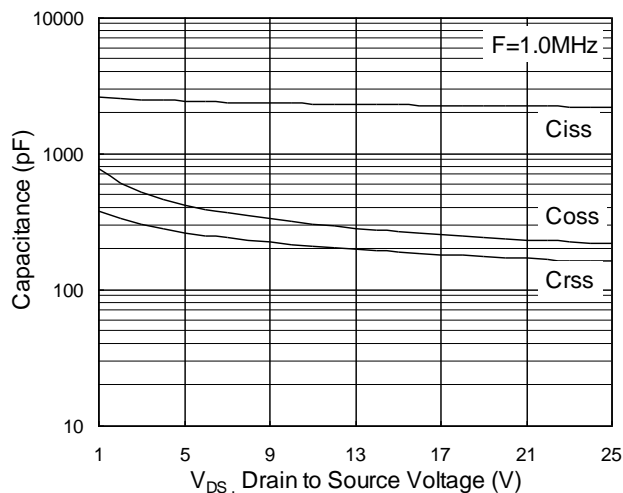


Fig.7 Capacitance

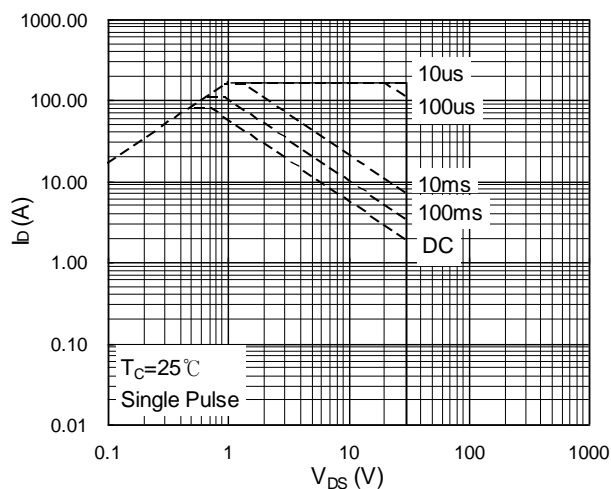


Fig.8 Safe Operating Area

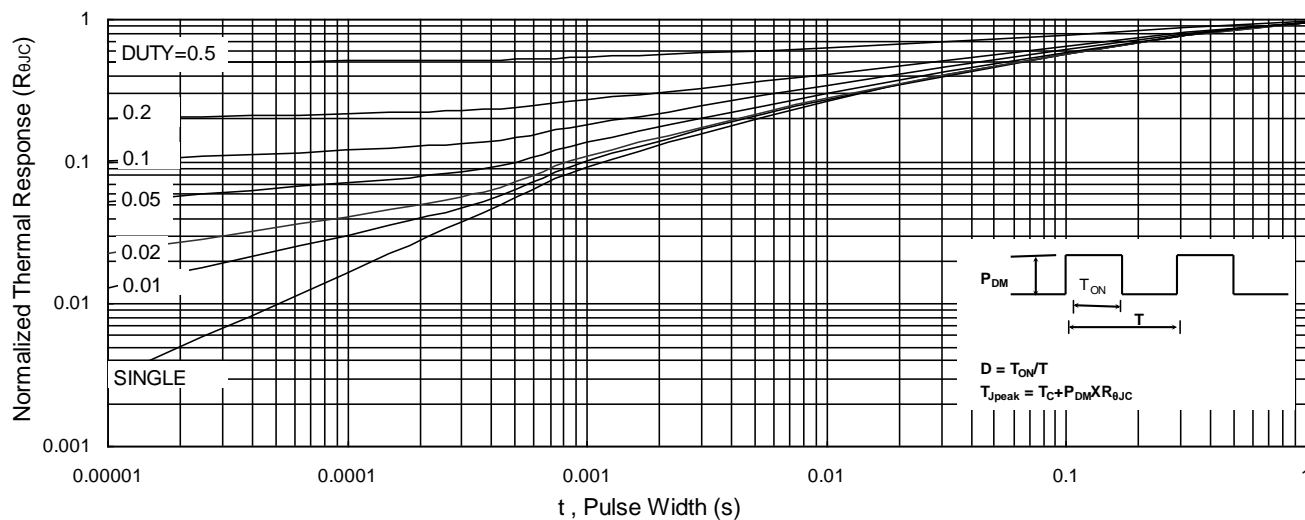


Fig.9 Normalized Maximum Transient Thermal Impedance

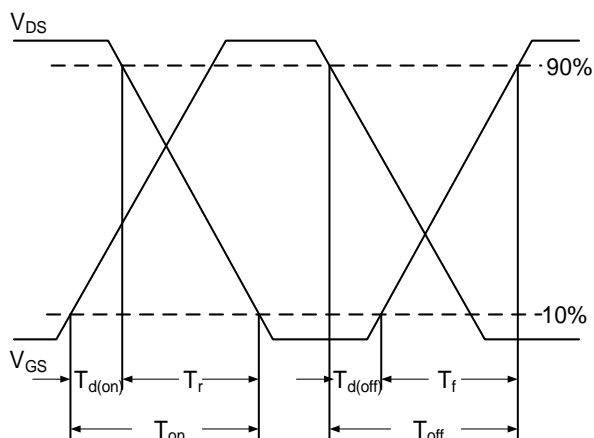


Fig.10 Switching Time Waveform

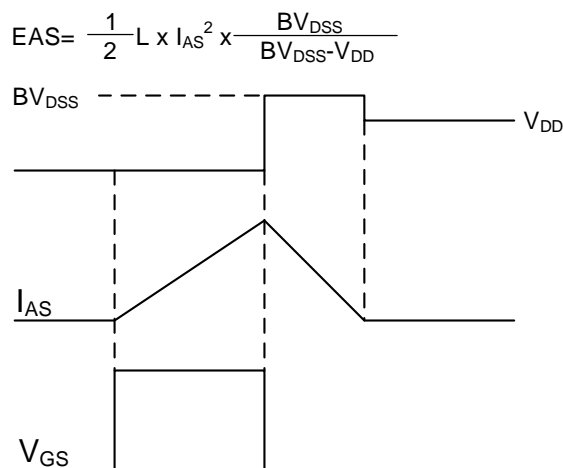
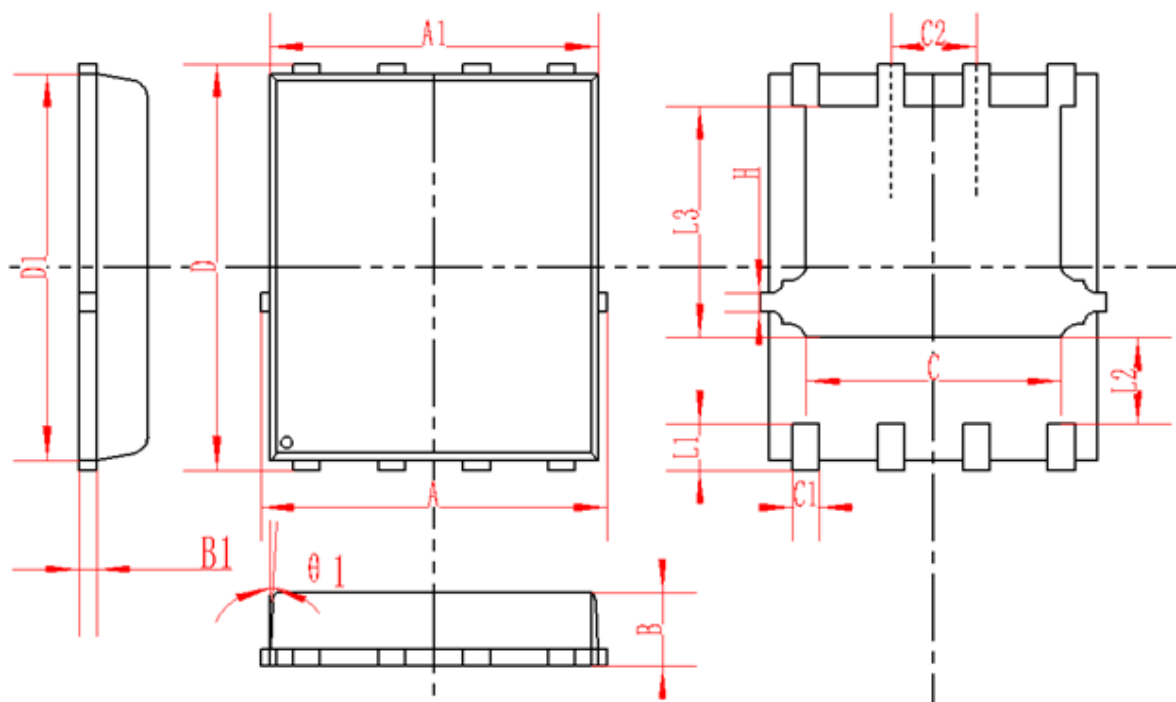


Fig.11 Unclamped Inductive Switching Waveform

$$EAS = \frac{1}{2} L \times I_{AS}^2 \times \frac{BV_{DSS}}{BV_{DSS} - V_{DD}}$$

DFN5X6-8L Package Information


SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX
A	4.95	5	5.05	0.195	0.197	0.199
A1	4.82	4.9	4.98	0.190	0.193	0.196
D	5.98	6	6.02	0.235	0.236	0.237
D1	5.67	5.75	5.83	0.223	0.226	0.230
B	0.9	0.95	1	0.035	0.037	0.039
B1	0.254REF			0.010REF		
C	3.95	4	4.05	0.156	0.157	0.159
C1	0.35	0.4	0.45	0.014	0.016	0.018
C2	1.27TYP			0.5TYP		
Ø1	8 _°	10 _°	12 _°	8 _°	10 _°	12 _°
L1	0.63	0.64	0.65	0.025	0.025	0.026
L2	1.2	1.3	1.4	0.047	0.051	0.055
L3	3.415	3.42	3.425	0.134	0.135	0.135
H	0.24	0.25	0.26	0.009	0.010	0.010

REEL SPECIFICATION

P/N	PKG	QTY
AON6362-MS	DFN5X6-8L	5000

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